

## Low voltage fast-switching NPN power transistor

#### **Features**

- Very low collector to emitter saturation voltage
- High current gain characteristic
- Fast-switching speed

### **Applications**

- Emergency lighting
- Voltage regulators
- Relay drivers
- High efficiency low voltage switching applications



The device is manufactured in NPN planar technology by using a "base island" layout. the resulting transistor shows exceptional high gain performance coupled with very low saturation voltage.

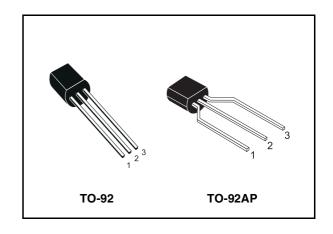


Figure 1. Internal schematic diagram

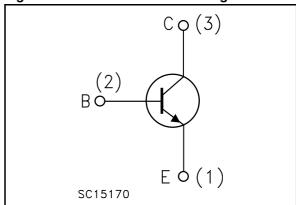


Table 1. Device summary

Order code	Marking	Package	Packaging
STSA851	SA851	TO-92	Bulk
STSA851-AP	SA851	TO-92AP	Ammopack

## **Contents**

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STSA851 Electrical ratings

# 1 Electrical ratings

Table 2. Absolute maximum rating

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-base voltage (I <sub>E</sub> = 0)	150	V
V <sub>CEO</sub>	Collector-emitter voltage (I <sub>B</sub> = 0)	60	V
V <sub>EBO</sub>	Emitter-base voltage ( $I_C = 0$ )	7	V
I <sub>C</sub>	Collector current	5	Α
I <sub>CM</sub>	Collector peak current (t <sub>P</sub> < 5 ms)	20	Α
I <sub>B</sub>	Base current	1	Α
P <sub>tot</sub>	Total dissipation at T <sub>amb</sub> = 25 °C	1.1	W
T <sub>stg</sub>	Storage temperature	-65 to 150	°C
T <sub>J</sub>	Max. operating junction temperature	150	°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R <sub>thj-amb</sub>	Thermal resistance junction-ambient max	114	°C/W

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Electrical characteristics STSA851

## 2 Electrical characteristics

 $(T_{case} = 25 \, ^{\circ}C \text{ unless otherwise specified})$ 

Table 4. Electrical characteristics

Symbol	Parameter	Test co	onditions	Min.	Тур.	Max.	Unit
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> = 120 V				50	nA
CBO	(I <sub>E</sub> = 0)	$V_{CB} = 120 \text{ V}$	$T_C = 100  ^{\circ}C$			1	μΑ
I <sub>EBO</sub>	Emitter cut-off current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 7 V				10	nA
V <sub>(BR)CBO</sub> (1)	Collector-base breakdown Voltage (I <sub>E</sub> = 0)	I <sub>C</sub> = 100 μA		150			٧
V <sub>(BR)CEO</sub> (1)	Collector-emitter breakdown Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 10 mA		60			V
V <sub>(BR)EBO</sub> (1)	Emitter-base breakdown Voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = 100 μA		7			V
		I <sub>C</sub> = 100 mA	$I_B = 5 \text{ mA}$		10	50	mV
V <sub>CE(sat)</sub> (1)	Collector-emitter	I <sub>C</sub> = 1 A	_		70	120	mV
	saturation voltage	$I_C = 2 A$	$I_B = 50 \text{ mA}$		140	200	mV
		I <sub>C</sub> = 5 A	$I_B = 200 \text{ mA}$		320	450	mV
V <sub>BE(sat)</sub> (1)	Base-emitter saturation voltage	I <sub>C</sub> = 4 A	I <sub>B</sub> = 200 mA		1	1.15	٧
		I <sub>C</sub> = 10 mA	$V_{CE} = 1 V$	150	300		
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = 2 A	$V_{CE} = 1 V$	150	270	350	
''FE	Do current gain	$I_C = 5 A$	$V_{CE} = 1 V$	90	140		
		I <sub>C</sub> = 10 A	$V_{CE} = 1 V$	30	50		
f <sub>T</sub>	Transition frequency	V <sub>CE</sub> = 10 V	I <sub>C</sub> = 100 mA		130		MHz
C <sub>CBO</sub>	Collector-base capacitance	V <sub>CB</sub> = 10 V	f = 1 MHz		45		pF
	Resistive load						
t <sub>on</sub>	Turn-on time	I <sub>C</sub> = 1 A	$V_{CC} = 10 \text{ V}$		55		ns
$t_{s}$	Storage time	$I_{B1} = -I_{B2} = 0.$	1 A		1.35		μs
t <sub>f</sub>	Fall time				120		ns

<sup>1.</sup> Pulsed duration = 300  $\mu$ s, duty cycle  $\geq$  1.5%.

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## 2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

Figure 3. DC current gain

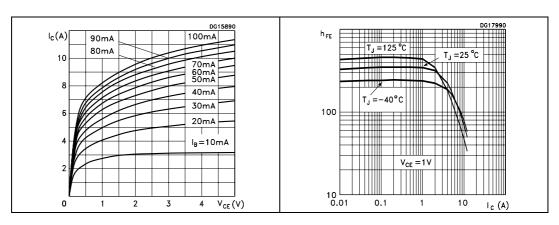


Figure 4. Collector-emitter saturation voltage

Figure 5. Collector-emitter saturation voltage

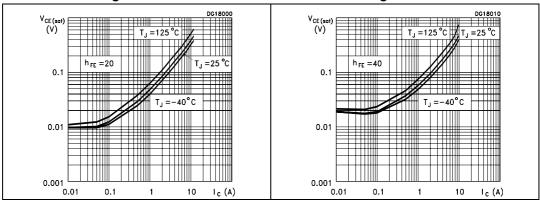
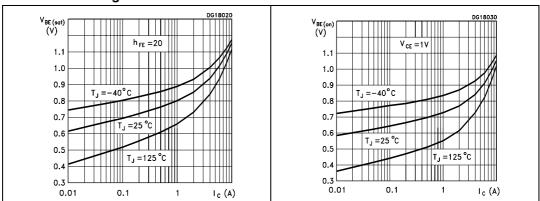


Figure 6. Base-emitter saturation voltage

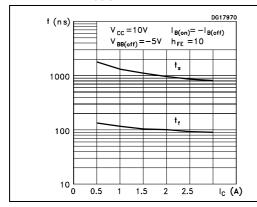
Figure 7. Base-emitter on voltage



Electrical characteristics STSA851

Figure 8. Switching times resistive load

Figure 9. Switching times resistive load



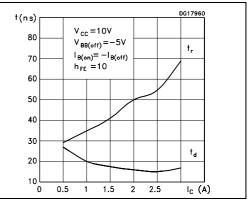
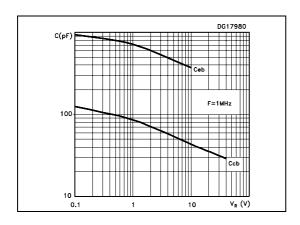
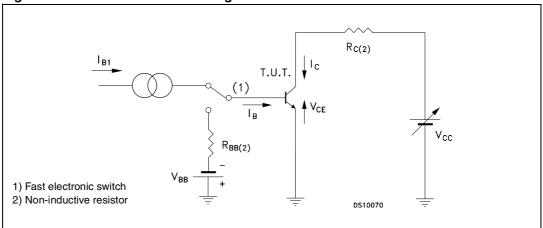


Figure 10. Capacitance



#### 2.2 Test circuit

Figure 11. Resistive load switching test circuit



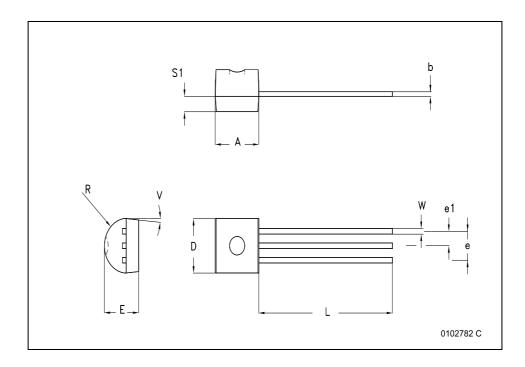
## 3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

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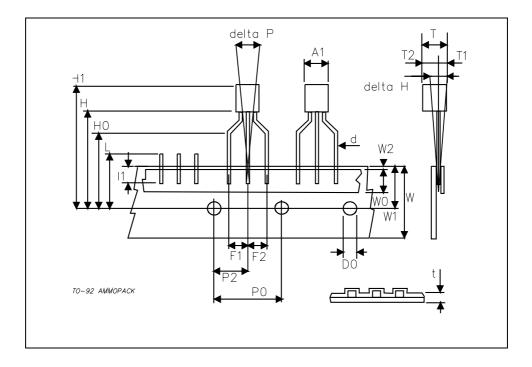
#### **TO-92 BULK SHIPMENT MECHANICAL DATA**

DIM	mm.				
DIM.	MIN.	ТҮР	MAX.		
А	4.32		4.95		
b	0.36		0.51		
D	4.45		4.95		
Е	3.30		3.94		
е	2.41		2.67		
e1	1.14		1.40		
L	12.70		15.49		
R	2.16		2.41		
S1	0.92		1.52		
W	0.41		0.56		
V		5 <sup>O</sup>			



#### TO-92 AMMOPACK SHIPMENT (Suffix"-AP") MECHANICAL DATA

DIM		mm.	
DIM.	MIN.	TYP	MAX.
A1			4.80
Т			3.80
T1			1.60
T2			2.30
d			0.48
P0	12.50	12.70	12.90
P2	5.65	6.35	7.05
F1,F2	2.44	2.54	2.94
delta H	-2.00		2.00
W	17.50	18.00	19.00
W0	5.70	6.00	6.30
W1	8.50	9.00	9.25
W2			0.50
Н	18.50		20.50
H0	15.50	16.00	16.50
H1			25.00
D0	3.80	4.00	4.20
t			0.90
L			11.00
I1	3.00		
delta P	-1.00		1.00



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Revision history STSA851

## 4 Revision history

Table 5. Document revision history

Date	Revision	Changes
05-Sep-2003	2	
25-Mar-2008	3	New graphics.

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